

TSMC-01-714



April 3, 2002

Commissioner of Patents and Trademarks
Washington, D.C. 20231

Fr: George O. Saile, Reg. No. 19,572
20 McIntosh Drive
Poughkeepsie, N.Y. 12603

A METHOD OF FORMING A STACKED CAPACITOR STRUCTURE WITH INCREASED SURFACE AREA FOR A DRAM DEVICE

Grp. Art Unit: 1765

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to comply with the duty of disclosure under CFR 1.97-1.99 and 37 CFR 1.56. Copies of each document is included herewith.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner of Patents and Trademarks, Washington, D.C. 20231, on April 1, 2002.

Stephen E. Ackerman, Reg. # 37761

U.S. Patent 6,025,225 to Forbes et al., "Circuits with a Trench Capacitor Having Micro-Roughened Semiconductor Surfaces and Methods for Forming the Same," discloses a trench cap process with roughened sides.

U.S. Patent 5,923,989 to Lin et al., "Method of Fabricating Rugged Capacitor of High Density DRAMs," reveals a stacked Cap process with Hemispherical grains (HSG).

U.S. Patent 5,691,221 to Jun, "Method for Manufacturing Semiconductor Memory Device Having a Stacked Capacitor," discloses a fin capacitor.

U.S. Patent 5,670,405 to Tseng, "Method of Making a Tooth Shaped Capacitor Using Ion Implantation," discloses a method of manufacturing a capacitor for use in semiconductor memories.

U.S. Patent 5,801,089 to Kenney, "Method of Forming Stacked Devices," discloses chips having subsurface structures within or adjacent to a horizontal trench in bulk single crystal semiconductors.

TSMC-01-714

U.S. Patent 6,057,205 to Wu, "Method to Form a Ragged Poly-Si Structure for High Density DRAM Cells," discloses a method for fabricating a capacitor on a semiconductor device.

Sincerely,


Stephen B. Ackerman, Reg. #37761

INFORMATION DISCLOSURE STATEMENT
IN AN APPLICATION

(Use several sheets if necessary)

TSMC 2

TSMC-01-714

101054,561

Bor-Wen Chan et al.

Flying Dutch

01/22/02

Groups and Unions

1765

U. S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

OTHER DOCUMENTS (including Author, Title, Date, Published Pages, etc.)

۱۲۷

2025 RELEASE UNDER E.O. 14176